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## List of Publications by Citations



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|---|---|---|---|
| 37 papers | 760 citations | 15 h-index | 27 g-index |
| 37 ext. papers | 873 ext. citations | 2.6 avg, IF | 3.95 L-index |

| # | Paper | IF | Citations |
|---|---|---|---|
| 37 | Annealing effects on the properties of copper oxide thin films prepared by chemical deposition. *Semiconductor Science and Technology*, **2005**, 20, 398-401 | 1.8 | 160 |
| 36 | The role of the interface insulator layer and interface states on the current-transport mechanism of Schottky diodes in wide temperature range. *Microelectronic Engineering*, **2006**, 83, 499-505 | 2.5 | 100 |
| 35 | Crossover from Nearest-Neighbor Hopping Conduction to Efros□Shklovskii Variable-Range Hopping Conduction in Hydrogenated Amorphous Silicon Films. *Japanese Journal of Applied Physics*, **2009**, 48, 111203 | 1.4 | 48 |
| 34 | The effects of film thickness on the optical properties of TiO2□SnO2compound thin films. *Physica Scripta*, **2011**, 84, 065602 | 2.6 | 42 |
| 33 | Studies on optical properties of antimony doped SnO 2 films. *Applied Surface Science*, **2015**, 352, 16-22 | 6.7 | 33 |
| 32 | Electron□Electron Interactions in Sb-Doped SnO2 Thin Films. *Journal of Electronic Materials*, **2010**, 39, 1152-1158 | 1.9 | 33 |
| 31 | . *IEEE Sensors Journal*, **2009**, 9, 263-270 | 4 | 31 |
| 30 | The thickness effect on the electrical conduction mechanism in titanium oxide thin films. *Journal of Alloys and Compounds*, **2010**, 493, 227-232 | 5.7 | 30 |
| 29 | Estimation of compensation ratio by identifying the presence of different hopping conduction mechanisms in SnO2 thin films. *Thin Solid Films*, **2011**, 519, 2302-2307 | 2.2 | 29 |
| 28 | Monitoring the characteristic properties of Ga-doped ZnO by Raman spectroscopy and atomic scale calculations. *Journal of Molecular Structure*, **2019**, 1180, 505-511 | 3.4 | 29 |
| 27 | Hopping conduction in In-doped CuO thin films. *Applied Surface Science*, **2014**, 318, 105-107 | 6.7 | 26 |
| 26 | Extraction of important electrical parameters of CuO. *Physica B: Condensed Matter*, **2011**, 406, 575-578 | 2.8 | 22 |
| 25 | Multiphonon hopping of carriers in CuO thin films. *Physica B: Condensed Matter*, **2011**, 406, 3551-3555 | 2.8 | 19 |
| 24 | Current-limiting property of Cu/cupric oxide/Cu sandwich structure. *Semiconductor Science and Technology*, **2002**, 17, 60-64 | 1.8 | 16 |
| 23 | Electrical And Microstructural Properties Of (Cu, Al, In)-Doped SnO2 Films Deposited By Spray Pyrolysis. *Advanced Materials Letters*, **2014**, 5, 309-314 | 2.4 | 15 |
| 22 | The change in the electrical transport mechanism from the grain boundary conduction to the nearest-neighbor hopping conduction in SnO2. *Journal of Materials Science: Materials in Electronics*, **2011**, 22, 872-875 | 2.1 | 12 |
| 21 | Fluctuating in the hopping rate of CuO thin films with respect to substrate temperature. *Superlattices and Microstructures*, **2012**, 52, 759-764 | 2.8 | 11 |

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| 20 | Effects of Co and Cu dopants on the structural, optical, and electrical properties of ZnO nanocrystals. *Journal of Materials Science: Materials in Electronics*, **2017**, 28, 6088-6092 | 2.1 | 10 |
| 19 | An Understanding of the Band Gap Shrinkage in Sn-Doped ZnO for Dye-Sensitized Solar Cells. *Journal of Electronic Materials*, **2017**, 46, 6739-6744 | 1.9 | 10 |
| 18 | Barrier-controlled electron transport in Sn-doped ZnO polycrystalline thin films. *Thin Solid Films*, **2012**, 522, 90-94 | 2.2 | 10 |
| 17 | The effect of humidity on electronic conductivity of an Au/CuO/Cu2O/Cu sandwich structure. *Semiconductor Science and Technology*, **2000**, 15, 112-116 | 1.8 | 10 |
| 16 | Electrical Properties of Polycrystalline SnO$_{2}$ Thin Films. *Applied Physics Express*, **2011**, 4, 121101 | 2.4 | 9 |
| 15 | Comprehensive structural analysis and electrical properties of (Cu, Al and In)-doped SnO2 thin films. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2019**, 251, 114445 | 3.1 | 9 |
| 14 | Determination of the critical carrier concentration for the metal–insulator transition in Ga-doped ZnO. *Journal of Materials Science: Materials in Electronics*, **2018**, 29, 14111-14115 | 2.1 | 9 |
| 13 | Al and X (Sn, Cu, In) co-doped ZnO nanocrystals. *Journal of Materials Science: Materials in Electronics* , **2016**, 27, 6179-6182 | 2.1 | 8 |
| 12 | Carrier transport in In-doped CuO thin films. *Philosophical Magazine*, **2013**, 93, 3110-3117 | 1.6 | 7 |
| 11 | High quality optoelectronic properties of Sb-doped SnO2 by spray pyrolysis with less solution. *Materials Research Express*, **2019**, 6, 086423 | 1.7 | 4 |
| 10 | Identification of Current Transport Mechanisms and Temperature Sensing Qualifications for Al/(ZnS-PVA)/p-Si Structures at Low and Moderate Temperatures. *IEEE Sensors Journal*, **2022**, 22, 99-106 | 4 | 4 |
| 9 | Influence of oxygen flow rate in CuO. *Applied Surface Science*, **2015**, 352, 155-157 | 6.7 | 3 |
| 8 | Investigation of the structural and optical properties of copper-titanium oxide thin films produced by changing the amount of copper. *Thin Solid Films*, **2019**, 685, 293-298 | 2.2 | 3 |
| 7 | Determination of the distribution of electronic states in hydrogenated amorphous germanium by capacitance techniques. *Semiconductor Science and Technology*, **2004**, 19, 270-276 | 1.8 | 2 |
| 6 | Effect of reverse-bias annealing on thermal equilibrium changes in hydrogenated amorphous germanium. *Semiconductor Science and Technology*, **1999**, 14, 1048-1051 | 1.8 | 2 |
| 5 | Enhancement of Nonlinear Absorption in Defect Controlled ZnO Polycrystalline Thin Films by Means of Co-Doping. *Physica Status Solidi (B): Basic Research*, **2021**, 258, 2000539 | 1.3 | 2 |
| 4 | The thermal equilibrium changes on reverse bias annealing in Schottky diodes. *Semiconductor Science and Technology*, **1997**, 12, 1451-1454 | 1.8 | 1 |
| 3 | Determination of thermal annealing effect in intrinsic a-Si:H film. *Journal of Non-Crystalline Solids*, **2000**, 276, 163-168 | 3.9 | 1 |

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| 2 | Comparison of characteristic properties of Al, Ga, and In-doped ZnO thin films formed by sol-gel method. *Superlattices and Microstructures*, **2021**, 159, 107034 | 2.8 | 0 |
| 1 | The investigation of an annealing effect on the density of states in a-Si:H film. *Semiconductor Science and Technology*, **1997**, 12, 291-295 | 1.8 | |